

# **Quad SPST CMOS Analog Switches**

#### **APPLICATIONS**

- · Audio switching
- Battery powered systems
- Data acquisition
- · Sample-and-hold circuits
- Telecommunication systems
- · Automatic test equipment
- Single supply circuits
- · Hard disk drives

#### **DESCRIPTION**

The DG444, DG445 monolithic quad analog switches are designed to provide high speed, low error switching of analog signals. The DG444 has a normally closed function. The DG445 has a normally open function. Combining low power (22 nW, typ.) with high speed (toN: 120 ns, typ.), the DG444, DG445 are ideally suited for upgrading DG211, DG212 sockets. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

To achieve high-voltage ratings and superior switching performance, the DG444, DG445 are built on Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply levels when off.

#### **FEATURES**

• Low on-resistance: 50  $\Omega$ 

Low leakage: 80 pA

Low power consumption: 22 nW
Fast switching action - t<sub>ON</sub>: 120 ns

· Low charge injection

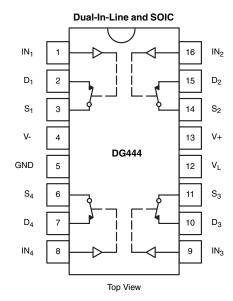
DG211, DG212 upgrades

• TTL/CMOS logic compatible

### **BENEFITS**

- · Low signal errors and distortion
- Reduced power supply requirements
- Faster throughput
- Improved reliability
- Reduced pedestal errors
- · Simple interfacing
- · Wide supply ranges
  - Single supply: +5 V to 36 V
  - Dual supplies: ± 5 V to ± 20 V

## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
LOGIC	DG444	DG445				
0	On	Off				
1	Off	On				

#### Note

 Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION						
TEMP. RANGE PACKAGE PART NUMBER						
	16-pin plastic DIP	DG444DJ				
-40 °C to 85 °C	10-pili piastic Die	DG445DJ				
-40 C t0 65 C	16 pip parrow SOIC	DG444DY				
	ro-pin narrow SOIC	16-pin narrow SOIC	DG445DY			



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<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER		LIMIT	UNIT		
V+ to V-		44			
GND to V-		25			
V <sub>L</sub>		(GND - 0.3) to (V+) +0.3	V		
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) -2 to (V+) +2 or 30 mA, whichever occurs first			
Continuous Current (Any Terminal)	ninal) 30		A		
Current, S or D (Pulsed at 1 ms, 10	% Duty Cycle)	100	– mA		
Storage Temperature		-65 to 125	°C		
Power Dissipation (Package) b	16-Pin Plastic DIP <sup>c</sup>	450	mW		
rower Dissipation (Package)	16-Pin Narrow Body SOIC <sup>d</sup>	640	11100		

## Notes

- $a. \ \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 8 mW/°C above 75 °C.

SPECIFICATIONS for Dual Supplies								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECI	RWISE SPECIFIED		<b>D SUFFIX</b> -40 °C TO 85 °C			UNIT
TANAMETEN	O'IMBOL	V+ = 15 V, V- = -15 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V$	е	TEMP. <sup>a</sup>	MIN. b	TYP. °	MAX. b	
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>			Full	-15	-	15	V
Drain-Source On-Resistanc e	R-ac	$I_S = -10 \text{ mA}, V_D = \pm 8.5 \text{ V}$		Room	-	50	85	Ω
Dialii-30dice Oil-nesistalic	R <sub>DS(on)</sub>	V+ = 13.5 V, V- = -13.5 V		Full	ı	-	100	52
	lov m			Room	-0.5	± 0.01	0.5	
Switch Off Leakage Current	I <sub>S(off)</sub>	V+ = 16.5, V- = -16.5 V		Full	-5	± 0.01	5	
Switch Off Leakage Current	1	$V_D = \pm 15.5 V, V_S = \pm 15.5$	V	Room	-0.5	± 0.01	0.5	nA
	I <sub>D(off)</sub>			Full	-5	± 0.01	5	nA
Channel On Leakage Current		V+ = 16.5 V, V- = -16.5 V	$V_{+} = 16.5 \text{ V}, V_{-} = -16.5 \text{ V}$ $V_{S} = V_{D} = \pm 15.5 \text{ V}$		-0.5	± 0.08	0.5	
Charmer On Leakage Current	I <sub>D(on)</sub>	$V_S = V_D = \pm 15.5 \text{ V}$			-10	± 0.08	10	
Digital Control								
Input Current V <sub>IN</sub> Low	I <sub>IL</sub>	$V_{IN}$ under test = 0.8 V All Other = 2.4 V		Full	-500	-0.01	500	n 1
Input Current V <sub>IN</sub> High	I <sub>IH</sub>	$V_{IN}$ under test = 2.4 V All Other = 0.8 V		Full	-500	0.01	500	- nA
Dynamic Characteristics								
Turn-On Time	t <sub>ON</sub>			Room	-	120	250	
Turn-Off Time		$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$ $V_S = \pm 10 \text{ V}, \text{ See Figure 2}$	DG444	Room	-	110	140	ns
rum-On Time	t <sub>OFF</sub>	V5 = ± 10 V, 000 Figure 2	DG445	Room	-	160	210	
Charge Injection <sup>e</sup>	Q	$C_L$ = 1 nF, $V_S$ = 0 V $V_{gen}$ = 0 V, $R_{gen}$ = 0 $\Omega$		Room	-	-1	-	рС
Off Isolation e	OIRR	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$		Room	-	60	-	٩D
Crosstalk (Channel-to-Channel) d	X <sub>TALK</sub>			Room	-	100	-	dB
Source Off Capacitance	C <sub>S(off)</sub>	f = 1 MHz		Room	-	4	-	
Drain Off Capacitance	C <sub>D(off)</sub>			Room	-	4	-	pF
Channel On Capacitance	C <sub>D(on)</sub>	V <sub>ANALOG</sub> = 0 V		Room	-	16	-	



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SPECIFICATIONS for Dual Supplies							
PARAMETER	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	<b>D SUFFIX</b> -40 °C TO 85 °C			UNIT	
	01202	V+ = 15 V, V- = -15 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^e$		MIN. b	TYP. c	MAX. b	
Power Supplies							
Positive Supply Current	I+		Room	-	0.001	1	
1 ositive Supply Current	17		Full	-	-	5	
Negative Supply Current	I-		Room	-1	-0.0001	ı	
Negative Supply Current	Į-	V+ = 16.5 V, V- = -16.5 V	Full	-5	ı	ı	μA
Logic Supply Current	I.	$V_{IN} = 0 \text{ V or } 5 \text{ V}$	Room	-	0.001	1	μΛ
Logic Supply Guirent	IL		Full	-	0.001	5	
Ground Current	la		Room	-1	-0.001	ı	
Ground Gurrent	I <sub>GND</sub>		Full	-5	-0.001	1	

SPECIFICATIONS for Unipolar Supplies								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	<b>LIMITS</b> -40 °C °C TO 85 °C			UNIT	
.,		V+ = 12 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^e$		MIN. b	TYP. °	MAX. b	ONIT	
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>		Full	0	-	12	V	
Drain-Source On-Resistance d		I <sub>S</sub> = -10 mA, V <sub>D</sub> = 3 V, 8 V V+ = 10.8 V, V <sub>L</sub> = 5.25 V	Room	-	100	160	Ω	
Drain-Source On-Resistance	R <sub>DS(on)</sub>		Full	-	-	200	52	
Dynamic Characteristics								
Turn-On Time	t <sub>ON</sub>	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}, V_S = 8 \text{ V}$	Room	-	300	450	no	
Turn-Off Time	t <sub>OFF</sub>	See Figure 2	Room	-	60	200	ns	
Charge Injection	Q	$C_L$ = 1 nF, $V_{gen}$ = 6 V, $R_{gen}$ = 0 $\Omega$	Room	-	2	-	рС	
Power Supplies								
Positive Supply Current	I+	V+ = 13.2 V, V <sub>IN</sub> = 0 V or 5 V	Room	-	0.001	1		
Positive Supply Current	1+	$v + = 13.2 \text{ v}, v_{1N} = 0 \text{ v or } 3 \text{ v}$	Full	-	-	5		
Nametica Complex Company	_	V <sub>IN</sub> = 0 V or 5 V	Room	-1	-0.0001	-		
Negative Supply Current	I-	VIN = 0 V OI 3 V	Full	-5	-	-		
Logic Supply Current	1.	V FOEV V OVER EV	Room	-	0.001	1	μA	
Logic Supply Current	IL	$V_L = 5.25 \text{ V}, V_{IN} = 0 \text{ V or } 5 \text{ V}$	Full	-	-	5		
Ground Current		V <sub>IN</sub> = 0 V or 5 V		Room	-1	-0.001	-	
Ground Current	I <sub>GND</sub>		Full	-5	-	-		

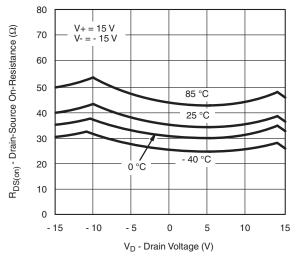
## Notes

- a. Room = 25 °C, Full = as determined by the operating temperature suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. Guaranteed by design, not subject to production test.
- e.  $V_{IN}$  = input voltage to perform proper function.

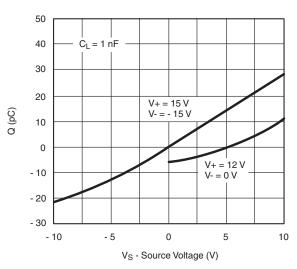
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



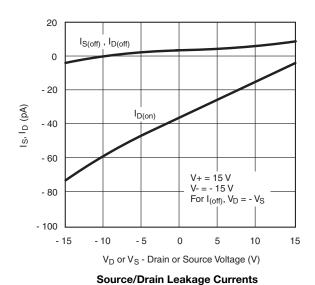
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

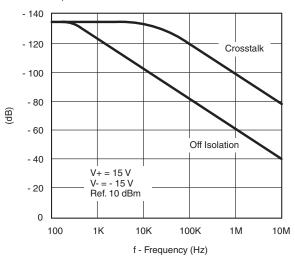


R<sub>DS(on)</sub> vs. V<sub>D</sub> and Temperature

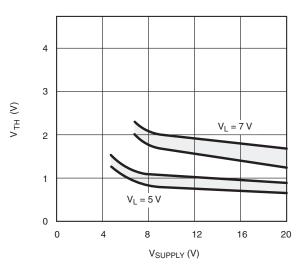


Charge Injection vs. Source Voltage

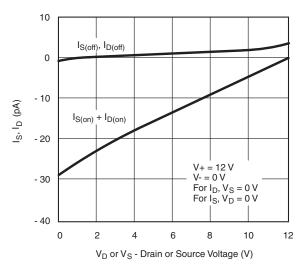




Crosstalk and Off Isolation vs. Frequency



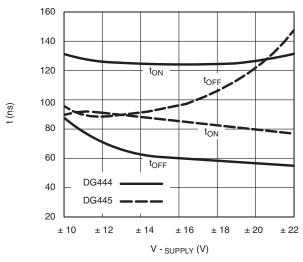
Switching Threshold vs. Supply Voltage



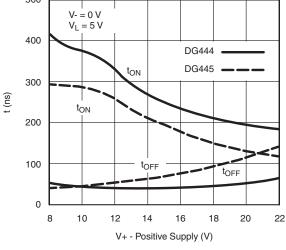
Source/Drain Leakage Currents (Single 12-V Supply)



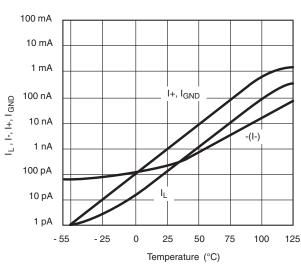
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



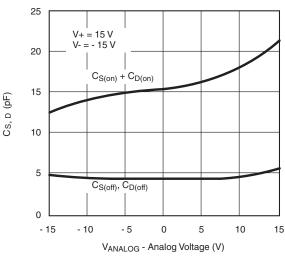
Switching Time vs. Power Supply Voltage



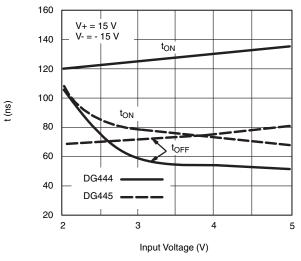
**Switching Times vs. Power Supply Voltage** 



Supply Current vs. Temperature



Source/Drain Capacitance vs. Analog Voltage



Switching Time vs. Input Voltage



## **SCHEMATIC DIAGRAM TYPICAL CHANNEL**

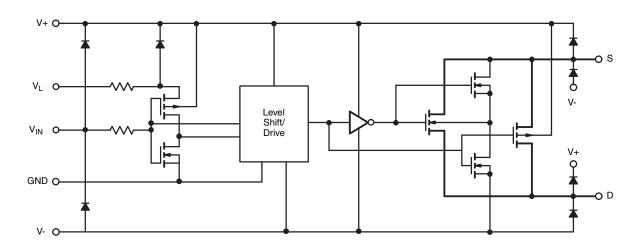


Fig. 1

## **TEST CIRCUITS**

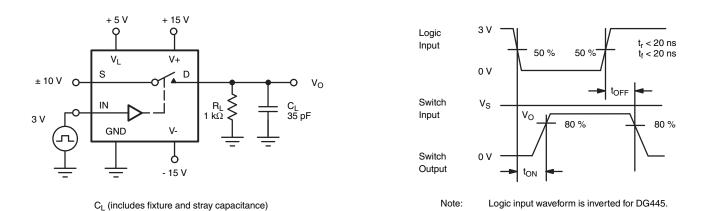


Fig. 2 - Switching Time

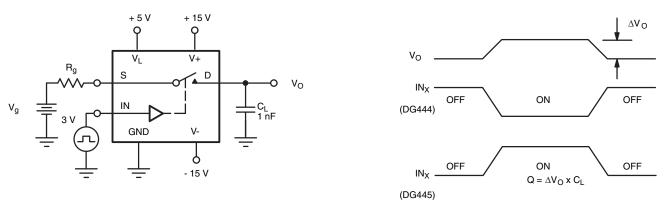


Fig. 3 - Charge Injection



## **TEST CIRCUITS**

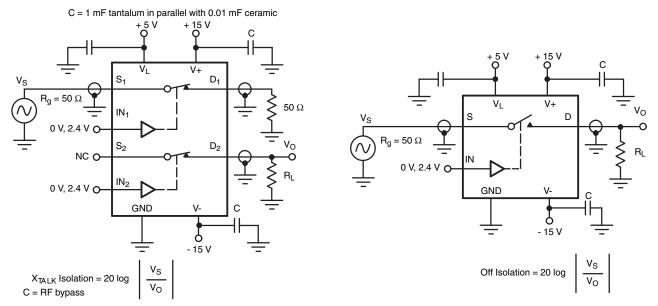


Fig. 4 - Crosstalk

Fig. 5 - Off Isolation

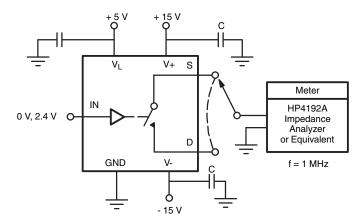


Fig. 6 - Source/Drain Capacitances

## **APPLICATIONS**

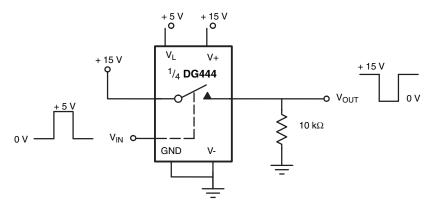


Fig. 7 - Level Shifter

## **APPLICATIONS**

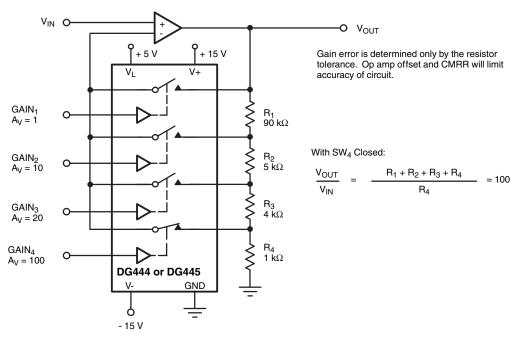


Fig. 8 - Precision-Weighted Resistor Programmable-Gain Amplifier

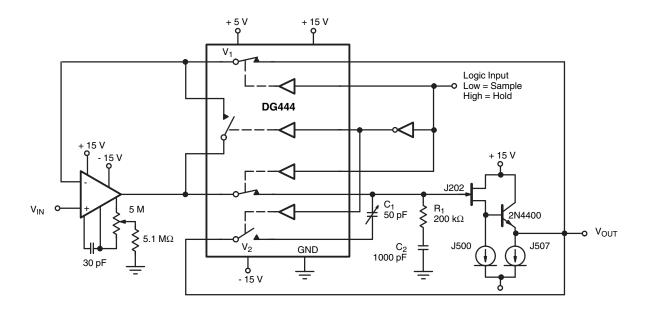


Fig. 9 - Precision Sample-and-Hold

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?70054">www.vishay.com/ppg?70054</a>.



SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012



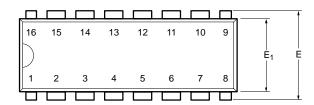
	MILLIM	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	1.35	1.75	0.053	0.069			
A <sub>1</sub>	0.10	0.20	0.004	0.008			
В	0.38	0.51	0.015	0.020			
С	0.18	0.23	0.007	0.009			
D	9.80	10.00	0.385	0.393			
E	3.80	4.00	0.149	0.157			
е	1.27	BSC	0.050	BSC			
Н	5.80	6.20	0.228	0.244			
L	0.50	0.93	0.020	0.037			
0	0°	8°	0°	8°			
ECN: S-0	ECN: S-03946—Rev. F, 09-Jul-01						

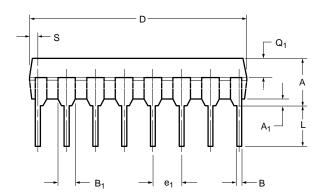
DWG: 5300

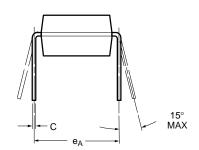




PDIP: 16-LEAD







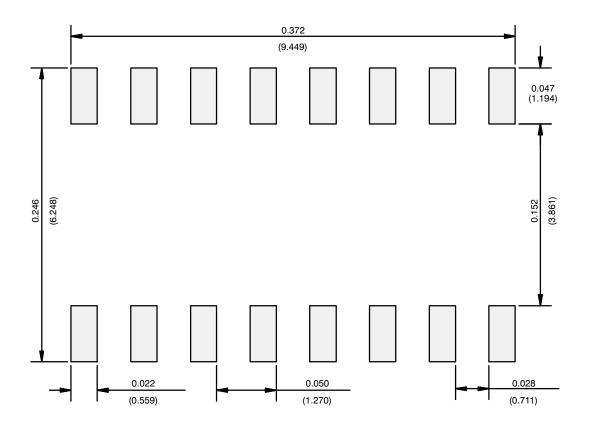
	MILLIN	IETERS	INC	HES				
Dim	Min	Max	Min	Max				
Α	3.81	5.08	0.150	0.200				
A <sub>1</sub>	0.38	1.27	0.015	0.050				
В	0.38	0.51	0.015	0.020				
B <sub>1</sub>	0.89	1.65	0.035	0.065				
С	0.20	0.30	0.008	0.012				
D	18.93	21.33	0.745	0.840				
E	7.62	8.26	0.300	0.325				
E <sub>1</sub>	5.59	7.11	0.220	0.280				
e <sub>1</sub>	2.29	2.79	0.090	0.110				
e <sub>A</sub>	7.37	7.87	0.290	0.310				
L	2.79	3.81	0.110	0.150				
Q <sub>1</sub>	1.27	2.03	0.050	0.080				
S	0.38	1.52	.015	0.060				
ECN: S-0	ECN: S-03946—Rev. D, 09-Jul-01							

DWG: 5482

Document Number: 71261 www.vishay.com 06-Jul-01



## **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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